# 10 kPa Uncompensated Silicon Pressure Sensors

The MPVZ12 series is a silicon piezoresistive pressure sensor providing a very accurate and linear voltage output — directly proportional to the applied pressure. This standard, low cost, uncompensated sensor permits manufacturers to design and add their own external temperature compensating and signal conditioning networks. Compensation techniques are simplified because of the predictability of Freescale's single element strain gauge design.

#### **Features**

- Low Cost
- Patented Silicon Shear Stress Strain Gauge Design
- · Ratiometric to Supply Voltage
- Easy to Use Chip Carrier Package Options
- · Differential and Gauge Options
- Durable Epoxy Package
- · Increased media compatibility fluorocarbon gel

#### **Application Examples**

- Air Movement Control
- Environmental Control Systems
- Level Indicators
- Leak Detection
- Medical Instrumentation
- Industrial Controls
- Pneumatic Control Systems
- Robotics

ORDERING INFORMATION <sup>(1)</sup>							
Device Type Options Case No. Order Number Device Mai							
Ported	Gauge	482A	MPVZ12GC6U	MPVZ12G			
		482C	MPVZ12GC7U	MPVZ12G			
		1735	MPVZ12GW6U	MZ12GW			
		1560	MPVZ12GW7U	MZ12GW			

 MPVZ12 series pressure sensors are available in differential and gauge configurations. Devices are available in the basic element package or with pressure port fittings which provide printed circuit board mounting ease and barbed hose pressure connections.

## **MPVZ12 SERIES**

UNCOMPENSATED PRESSURE SENSOR 0 TO 10 kPA (0-1.45 psi) 55 mV FULL SCALE SPAN (TYPICAL)

#### SMALL OUTLINE PACKAGE



MPVZ12GC6U **CASE 482A-01** 



MPVZ12GC7U **CASE 482C-03** 



MPVZ12GW6U **CASE 1735-01** 



MPVZ12GW7U **CASE 1560-02** 

PIN NUMBERS					
1	GND	5	N/C		
2	+V <sub>out</sub>	6	N/C		
3	V <sub>s</sub>	7	N/C		
4	–V <sub>out</sub>	8	N/C		

NOTE: Pin 1 is noted by the notch in the lead.



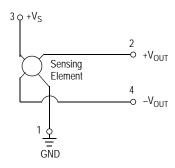


Figure 1. Uncompensated Pressure Sensor Schematic

#### **VOLTAGE OUTPUT VERSUS APPLIED DIFFERENTIAL PRESSURE**

The output voltage of the differential or gauge sensor increases with increasing pressure applied to the pressure side (P1) relative to the vacuum side (P2). Similarly, output

voltage increases as increasing vacuum is applied to the vacuum side (P2) relative to the pressure side (P1).

Table 1. Maximum Ratings<sup>(1)</sup>

Rating	Symbol	Value	Unit
Maximum Pressure (P1 > P2)	P <sub>MAX</sub>	75	kPa
Burst Pressure (P1 > P2)	P <sub>BURST</sub>	100	kPa
Storage Temperature	T <sub>STG</sub>	-40 to +125	°C
Operating Temperature	T <sub>A</sub>	-40 to +125	°C

<sup>1.</sup> Exposure beyond the specified limits may cause permanent damage or degradation to the device.

Table 2. Operating Characteristics ( $V_S = 3.0 \text{ Vdc}$ ,  $T_A = 25^{\circ}\text{C}$  unless otherwise noted, P1 > P2)

Characteristic	Symbol	Min	Тур	Max	Unit
Differential Pressure Range <sup>(1)</sup>	P <sub>OP</sub>	0	_	10	kPa
Supply Voltage <sup>(2)</sup>	V <sub>S</sub>	_	3.0	6.0	Vdc
Supply Current	I <sub>o</sub>	_	6.0	_	mAdc
Full Scale Span <sup>(3)</sup>	V <sub>FSS</sub>	45	55	70	mV
Offset <sup>(4)</sup>	V <sub>off</sub>	0	20	35	mV
Sensitivity	ΔV/ΔΡ	_	5.5	_	mV/kPa
Linearity <sup>(5)</sup>	_	-0.5	_	0.5	%V <sub>FSS</sub>
Pressure Hysteresis <sup>6</sup> (0 to 10 kPa)	_	_	±0.1	_	%V <sub>FSS</sub>
Temperature Hysteresis <sup>(5)</sup> (–40°C to +125°C)	_	_	±0.5	_	%V <sub>FSS</sub>
Temperature Coefficient of Full Scale Span <sup>(5)</sup>	TCV <sub>FSS</sub>	-0.22	_	-0.16	%V <sub>FSS</sub> /°C
Temperature Coefficient of Offset <sup>(5)</sup>	TCV <sub>off</sub>	_	±15	_	μV/°C
Temperature Coefficient of Resistance <sup>(5)</sup>	TCR	0.28	_	0.34	%Z <sub>in</sub> /°C
Input Impedance	Z <sub>in</sub>	400	_	550	W
Output Impedance	Z <sub>out</sub>	750	_	1250	W
Response Time <sup>(6)</sup> (10% to 90%)	t <sub>R</sub>	_	1.0	_	ms
Warm-Up Time <sup>(7)</sup>	_	_	20	_	ms
Offset Stability <sup>(8)</sup>	_	_	±0.5	_	%V <sub>FSS</sub>

- 1. 1.0 kPa (kiloPascal) equals 0.145 psi.
- 2. Device is ratiometric within this specified excitation range. Operating the device above the specified excitation range may induce additional error due to device self-heating.
- Full Scale Span (V<sub>FSS</sub>) is defined as the algebraic difference between the output voltage at full rated pressure and the output voltage at the minimum related pressure.
- 4. Offset (V<sub>OFF</sub>) is defined as the output voltage at the minimum rated pressure.
- 5. Accuracy (error budget) consists of the following:
  - Linearity: Output deviation from a straight line relationship with pressure, using end point method, over the specified pressure range.
  - Temperature Hysteresis: Output deviation at any temperature within the operating temperature range, after the temperature is cycled to

and from the minimum or maximum operating temperature points, with zero differential pressure applied.

• Pressure Hysteresis: Output deviation at any pressure with the specified range, when this pressure is cycled to and from the minimum

or maximum rated pressure at 25°C.

• TcSpan: Output deviation at full rated pressure over the temperature range of 0 to 85°C, relative to 25°C.

TcOffset: Output deviation with minimum rated pressure applied, over the temperature range of 0 to 85°C, relative to 25°C.
 TCR: Z<sub>IN</sub> deviation with minimum rated pressure applied, over the temperature range of -40°C to ±125°C, relative to

25°C.

- 6. Response Time is defined as the time form the incremental change in the output to go from 10% to 90% of its final value when subjected to a specified step change in pressure.
- 7. Warm-up Time is defined as the time required for the product to meet the specified output voltage after the pressure is stabilized.
- 8. Offset stability is the product's output deviation when subjected to 1000 hours of Pulsed Pressure, Temperature Cycling with Bias Test.

#### **TEMPERATURE COMPENSATION**

Figure 2 shows the typical output characteristics of the MPVZ12 series over temperature.

Because this strain gauge is an integral part of the silicon diaphragm, there are no temperature effects due to differences in the thermal expansion of the strain gauge and the diaphragm, as are often encountered in bonded strain gauge pressure sensors. However, the properties of the strain gauge itself are temperature dependent, requiring that the device be temperature compensated if it is to be used over an extensive temperature range.

Temperature compensation and offset calibration can be achieved rather simply with additional resistive components, or by designing your system using the MPX2010D series sensor.

Several approaches to external temperature compensation over both –40 to +125°C and 0 to +80°C ranges are presented in Applications Note AN840.

#### **LINEARITY**

Linearity refers to how well a transducer's output follows the equation:  $V_{out} = V_{off} + \text{sensitivity x P}$  over the operating pressure range (Figure 3). There are two basic methods for calculating nonlinearity: (1) end point straight line fit or (2) a least squares best line fit. While a least squares fit gives the "best case" linearity error (lower numerical value), the calculations required are burdensome.

Conversely, an end point fit will give the "worst case" error (often more desirable in error budget calculations) and the calculations are more straightforward for the user. Freescale's specified pressure sensor linearities are based on the end point straight line method measured at the midrange pressure.

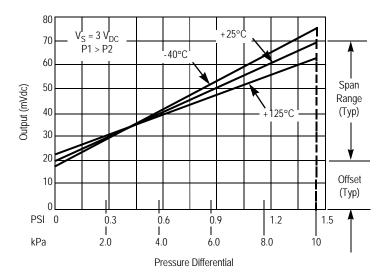


Figure 2. Output versus Pressure Differential

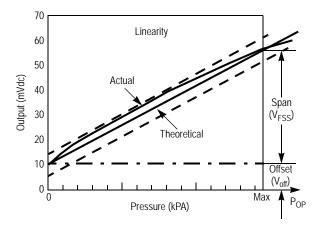


Figure 3. Linearity Specification Comparison

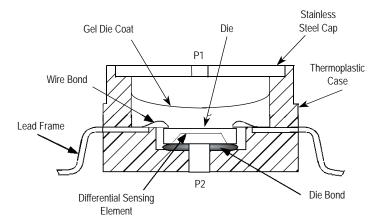


Figure 4. Cross-Sectional Diagram (not to scale)

Figure 4 illustrates the differential or gauge configuration in the basic chip carrier (applicable to cases 482, 1560 and 1735). A gel isolates the die surface and wire bonds from the environment, while allowing the pressure signal to be transmitted to the silicon diaphragm.

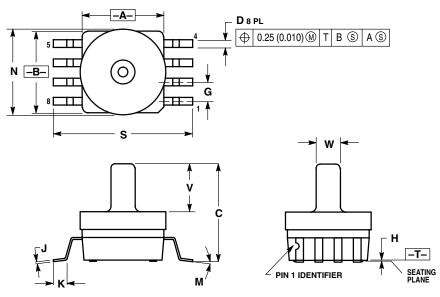
Operating characteristics, internal reliability and qualification tests are based on use of dry clean air as the pressure media. Media other than dry clean air may have adverse effects on sensor performance and long term reliability. Contact the factory for information regarding media compatibility in your application.

#### PRESSURE (P1)/VACUUM (P2) SIDE IDENTIFICATION TABLE

Freescale designates the two sides of the pressure sensor as the Pressure (P1) side and the Vacuum (P2) side. The Pressure (P1) side is the side containing gel which isolates the die from the environment. The Freescale MPVZ12 series is designed to operate with positive differential pressure applied, P1 > P2.

The Pressure (P1) side may be identified by using the following table

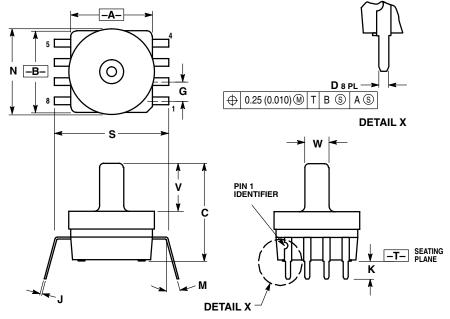
Part Number	Case Type	Pressure (P1) Side Identifier
MPVZ12GC6U	482A 98ASB17757C	Top with Port Attached
MPVZ12GC7U	482C 98ASB17759C	Top with Port Attached
MPVZ12GW6U	1735 98ASA10686D	Top with Port Attached
MPVZ12GW7U	1560 98ASA10611D	Top with Port Attached



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006).
  5. ALL VERTICAL SURFACES S° TYPICAL DRAFT.

	INCHES		MILLIN	ETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.415	0.425	10.54	10.79	
В	0.415	0.425	10.54	10.79	
С	0.500	0.520	12.70	13.21	
D	0.038	0.042	0.96	1.07	
G	0.100	BSC	2.54	BSC	
Н	0.002	0.010	0.05	0.25	
J	0.009	0.011	0.23	0.28	
K	0.061	0.071	1.55	1.80	
M	0 °	7°	0 °	7 °	
N	0.444	0.448	11.28	11.38	
S	0.709	0.725	18.01	18.41	
٧	0.245	0.255	6.22	6.48	
W	0.115	0.125	2.92	3.17	

**CASE 482A-01 ISSUE A SMALL OUTLINE PACKAGE** 



**CASE 482C-03 ISSUE B SMALL OUTLINE PACKAGE** 

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: INCH.

  3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.

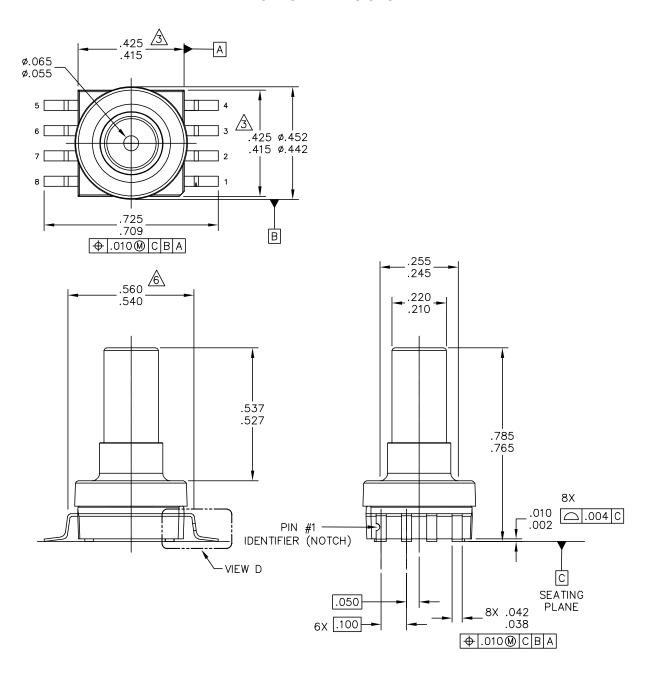
- PHOTHUSION.

  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006).

  5. ALL VERTICAL SURFACES 5° TYPICAL DRAFT.

  6. DIMENSION S TO CENTER OF LEAD WHEN FORMED PARALLEL.

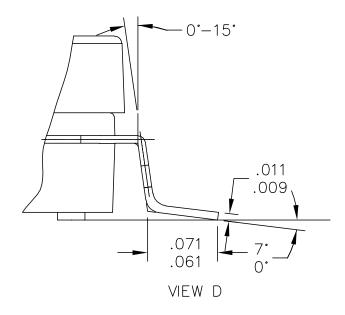
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.415	0.425	10.54	10.79
В	0.415	0.425	10.54	10.79
С	0.500	0.520	12.70	13.21
D	0.026	0.034	0.66	0.864
G	0.100	BSC	2.54 BSC	
J	0.009	0.011	0.23	0.28
K	0.100	0.120	2.54	3.05
М	0°	15 °	0 °	15 °
N	0.444	0.448	11.28	11.38
S	0.540	0.560	13.72	14.22
٧	0.245	0.255	6.22	6.48
W	0.115	0.125	2.92	3.17
	2.770			



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TITLE:		DOCUMENT NO	): 98ASA10686D	REV: A
SO, 8 I/O, .420 X .420 PKG, .100 IN PITCH		CASE NUMBER	t: 1735–01	16 AUG 2005
		STANDARD: NO	N-JEDEC	

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MPVZ12



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		STANDARD: NO	N-JEDEC	

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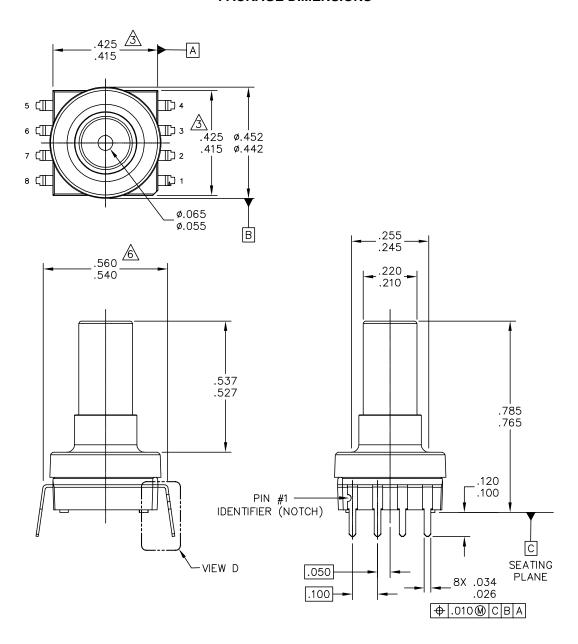
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.
- A. DIMENSIONS DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION IS .006.
- 5. ALL VERTICAL SURFACES 5' TYPICAL DRAFT.
- 6 DIMENSION TO CENTER OF LEAD WHEN FORMED PARALLEL.

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		STANDARD: NO	N-JEDEC	

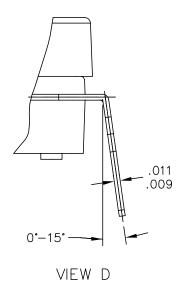
#### CASE 1735-01 ISSUE A SMALL OUTLINE PACKAGE

MPVZ12



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SO, 8 I/O, .420 X .420 PKG, .100 IN PITCH		CASE NUMBER	2: 1560–02	26 MAY 2005
		STANDARD: NO	N-JEDEC	

#### CASE 1560-02 ISSUE C SMALL OUTLINE PACKAGE



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TITLE:		DOCUMENT NO	): 98ASA10611D	REV: C
SO, 8 I/O, .420 X .4		CASE NUMBER	: 1560–02	26 MAY 2005
.100 IN PITCH		STANDARD: NO	N-JEDEC	

#### CASE 1560-02 ISSUE C SMALL OUTLINE PACKAGE

MPVZ12

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
- 2. CONTROLLING DIMENSION: INCH.

- 4. MAXIMUM MOLD PROTRUSION IS .006.
- 5. ALL VERTICAL SURFACES 5' TYPICAL DRAFT.

6 DIMENSION TO CENTER OF LEAD WHEN FORMED PARALLEL.

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		CASE NUMBER	2: 1560–02	26 MAY 2005
		STANDARD: NON-JEDEC		

#### CASE 1560-02 ISSUE C SMALL OUTLINE PACKAGE

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